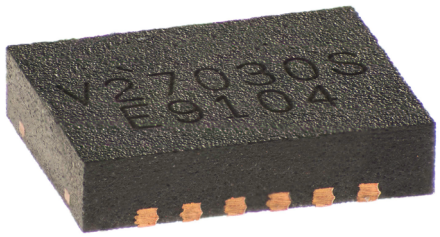
CGHV27030S

30 W, DC - 6.0 GHz, GaN HEMT



Package Type: 3x4 DFN
PN: CGHV27030S

Description

The CGHV27030S is an unmatched, gallium nitride (GaN) high electron mobility transistor (HEMT) which offers high efficiency, high gain and wide bandwidth capabilities. The CGHV27030S GaN HEMT devices are ideal for telecommunications applications with frequencies of 700-960 MHz, 1200-1400 MHz, 1800-2200 MHz, 2500-2700 MHz, and 3300-3700 MHz at both 50 V and 28 V operations. The CGHV27030S is also ideal for tactical communications applications operating from 20-2500 MHz, including land mobile radios. Additional applications include L-Band RADAR and S-Band RADAR. The CGHV27030S can operate with either a 50 V or 28 V rail. The transistor is available in a 3mm x 4mm, surface mount, dual-flat-no-lead (DFN) package.

Typical Performance 2.5-2.7 GHz (T_C = 25°C), 50 V

Parameter	2.5 GHz	2.6 GHz	2.7 GHz	Units
Small Signal Gain	22.5	22.0	21.4	dB
Adjacent Channel Power @ P_{AVE} = 5 W	-34.5	-35.0	-34.0	dBc
Drain Efficiency @ P_{AVE} = 5 W	28.5	29.5	30.0	%
Input Return Loss	8.5	14	14	dB

Note: Measured in the CGHV27030S-AMP1 application circuit, under 7.5 dB PAR single carrier WCDMA signal test model 1 with 64 DPCH

Features for 50 V in CGHV27030S-AMP1

- 2.5 - 2.7 GHz Operation
- 30 W Typical Output Power
- 20 dB Gain at 5 W P_{AVE}
- -34 dBc ACLR at 5 W P_{AVE}
- 30% efficiency at 5 W P_{AVE}
- High degree of APD and DPD correction can be applied

Listing of Available Hardware Application Circuits / Demonstration Circuits

Application Circuit	Operating Frequency	Amplifier Class	Operating Voltage
CGHV27030S-AMP1	2.5 - 2.7 GHz	Class A/B	50 V
CGHV27030S-AMP2			28 V
CGHV27030S-AMP3	1.8 - 2.2 GHz		
CGHV27030S-AMP4			50 V
CGHV27030S-AMP5	1.2 - 1.4 GHz		

Large Signal Models Available for ADS and MWO

RoHS compliant

Rev. 7, August 2024

Absolute Maximum Ratings (not simultaneous) at 25°C Case Temperature

Parameter	Symbol	Rating	Units	Conditions
Drain-Source Voltage	V_{DSS}	150	V	25°C
Gate-to-Source Voltage	V_{GS}	-10, +2		
Storage Temperature	T_{STG}	-65, +150	°C	
Operating Junction Temperature	T_J	225		
Maximum Forward Gate Current	I_{GMAX}	4	mA	25°C
Maximum Drain Current[1]	I_{DMAX}	1.5	A	
Soldering Temperature[2]	T_S	245	°C	
Case Operating Temperature[3]	T_C	-40, +150		
Thermal Resistance, Junction to Case[4]	$R_{\theta JC}$	6.18	°C/W	85°C

Notes:
[1] Current limit for long term, reliable operation
[2] Refer to the Application Note on soldering
[3] T_C = Case temperature for the device. It refers to the temperature at the ground tab underneath the package. The PCB will add additional thermal resistance

[4] Measured for the CGHV27030S at P_{DISS} = 12 W

The R_{TH} for the demonstration amplifier, CGHV27030S-AMP1, with 33 x 0.011 via holes designed on a 20 mil thick Rogers 4350 PCB, is 3.9°C. The total R_{TH} from the heat sink to the junction is 6.18°C + 3.9°C = 10.08°C/W

Electrical Characteristics (T_C = 25°C)

Characteristics	Symbol	Min.	Typ.	Max.	Units	Conditions
DC Characteristics[1]						
Gate Threshold Voltage	$V_{GS(th)}$	-3.8	-3.0	-2.3	V_{DC}	V_{DS} = 10 V, I_D = 4 mA
Gate Quiescent Voltage	$V_{GS(Q)}$	—	-2.7	—		V_{DS} = 50 V, I_D = 0.13 A
Saturated Drain Current	I_{DS}	2.6	3.7	—	A	V_{DS} = 6.0 V, V_{GS} = 2.0 V
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	125	—	—	V_{DC}	V_{GS} = -8 V, I_D = 4 mA
RF Characteristics[3] (T_C = 25°C, F_0 = 2.65 GHz unless otherwise noted)						
Gain	G	20	23	—	dB	V_{DD} = 50 V, I_{DQ} = 0.13 A, P_{IN} = 10 dBm
Output Power[4]	P_{OUT}	44.5	45	—	dBm	V_{DD} = 50 V, I_{DQ} = 0.13 A, P_{IN} = 28 dBm
Drain Efficiency[4]	η	64	73	—	%	
Output Mismatch Stress[4]	VSWR	—	10 : 1	—	Ψ	No damage at all phase angles, V_{DD} = 50 V, I_{DQ} = 0.13 A, P_{IN} = 28 dBm
Dynamic Characteristics						
Input Capacitance[5]	C_{GS}	—	5.38	—	pF	V_{DS} = 50 V, V_{GS} = -8 V, f = 1 MHz
Output Capacitance[5]	C_{DS}	—	1.18	—		
Feedback Capacitance	C_{GD}	—	0.12	—		

Notes:
[1] Measured on wafer prior to packaging
[2] Scaled from PCM data
[3] Measured in the production test fixture. This fixture is designed for high volume test at 2.65 GHz
[4] Un-modulated Pulsed Signal 100 µs, 10% duty cycle
[5] Includes package parasitics

Typical Performance in Application Circuit CGHV27030S-AMP1

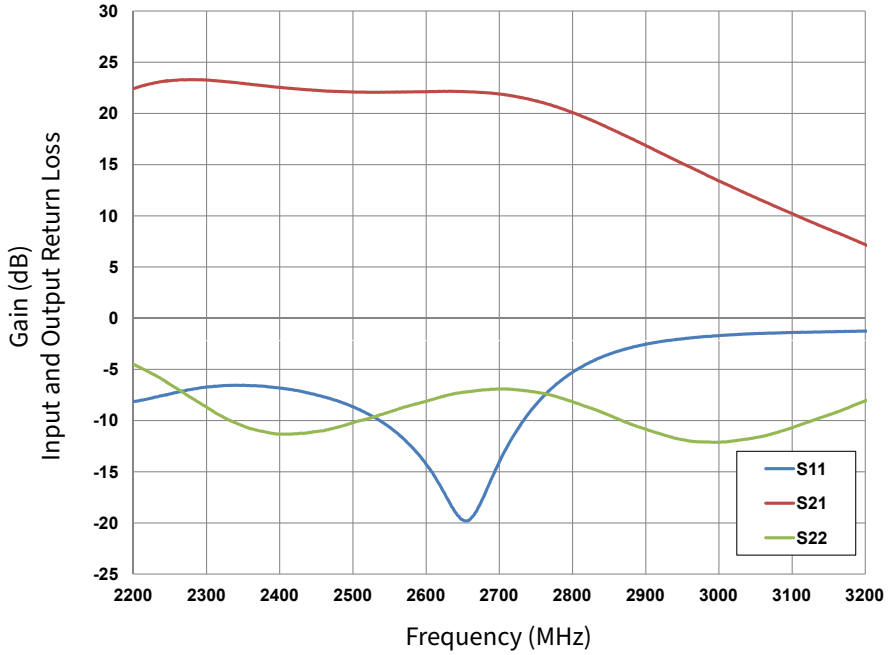


Figure 1. Small Signal Gain and Return Losses vs Frequency
V_{DD} = 50 V, I_{DQ} = 0.13 A

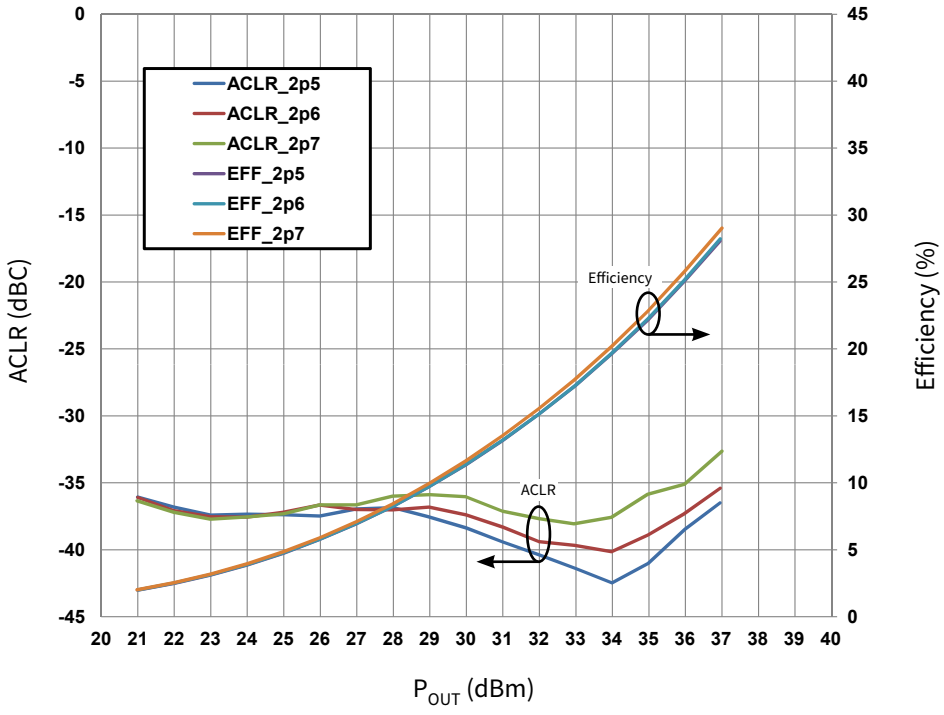


Figure 2. Typical Drain Efficiency and ACLR vs. Output Power
V_{DD} = 50 V, I_{DQ} = 0.13 A, 1c WCDMA, PAR = 7.5 dB

Typical Performance in Application Circuit CGHV27030S-AMP1

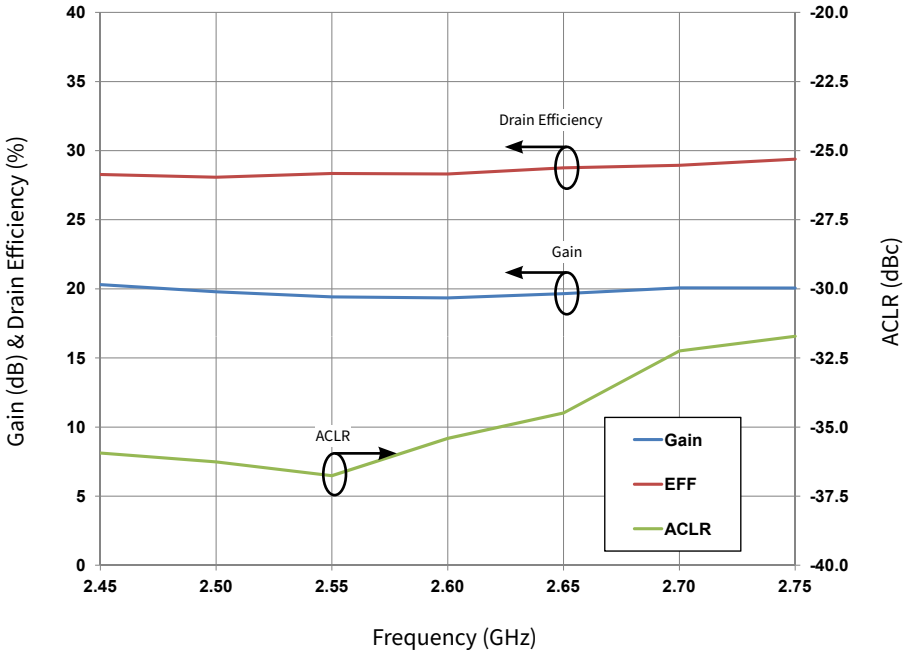
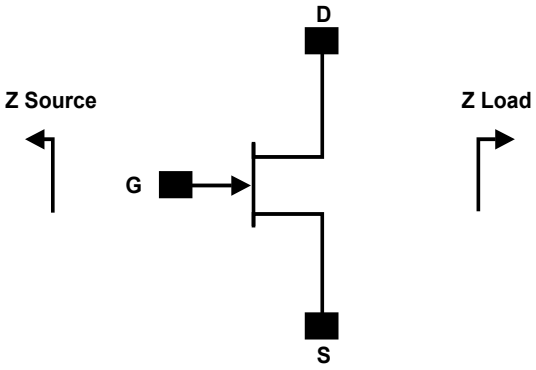


Figure 3. Typical Gain, Drain Efficiency and ACLR vs Frequency
V_{DD} = 50 V , I_{DQ} = 0.13 A, P_{AVE} = 5 W, 1c WCDMA, PAR = 7.5 dB

Source and Load Impedances for Application Circuit CGHV27030S-AMP1



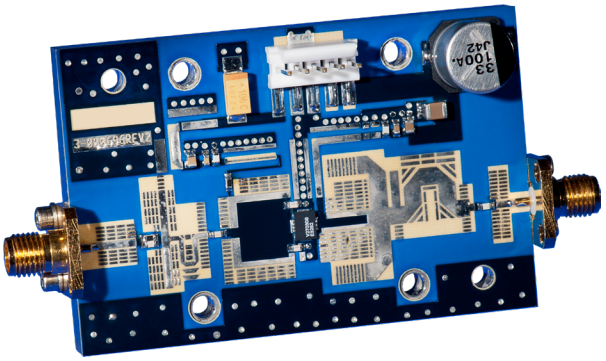
Frequency (MHz)	Z Source	Z Load
2500	5.69 + j7.82	10.9 + j15.7
2600	2.8 - j1.1	11.5 + j16.7
2700	2.5 - j1.7	12.1 + j17.7

Notes:
[1] V_{DD} = 50 V, I_{DQ} = 0.13 A in the DFN package
[2] Impedances are extracted from the CGHV27030S-AMP1 application circuit and are not source and load pull data derived from the transistor

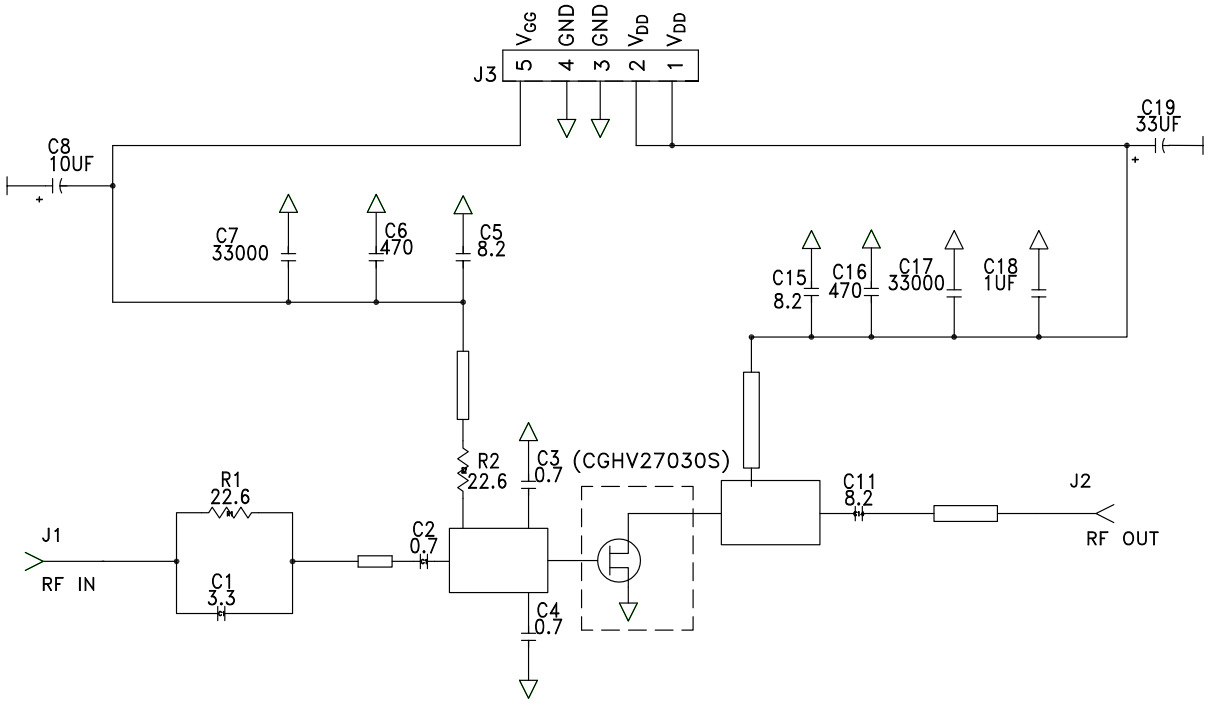
CGHV27030S-AMP1 Bill of Materials

Designator	Description	Qty
R1, R2	RES, 22.6 ohm, +/-1%, 1/16W, 0603	2
C1	CAP, 3.3 pF, ±0.1 pF, 0603, ATC	1
C2	CAP, 1.1 pF, ±0.05 pF, 0603, ATC	1
C3, C4	CAP, 0.7 pF, ±0.05 pF, 0603, ATC	3
C5, C11, C15	CAP, 8.2 pF, ±0.25 pF, 0603, ATC	3
C6, C16	CAP, 470 pF, 5%, 100 V, 0603	2
C7, C17	CAP, 33000 pF, 0805, 100 V, 0603, X7R	2
C18	CAP, 1.0 µF, 100 V, 10%, X7R, 1210	1
C8	CAP, 10 µF, 16 V, TANTALUM	1
C19	CAP, 33 µF, 20%, G CASE	1
J1, J2	CONN, SMA, PANEL MOUNT JACK, FLANGE, 4-HOLE, BLUNT POST	2
J3	HEADER RT>PLZ .1CEN LK 5 POS	1
PCB	PCB, ROGERS 4350, ER 3.66	1
Q1	CGHV27030S, QFN	1

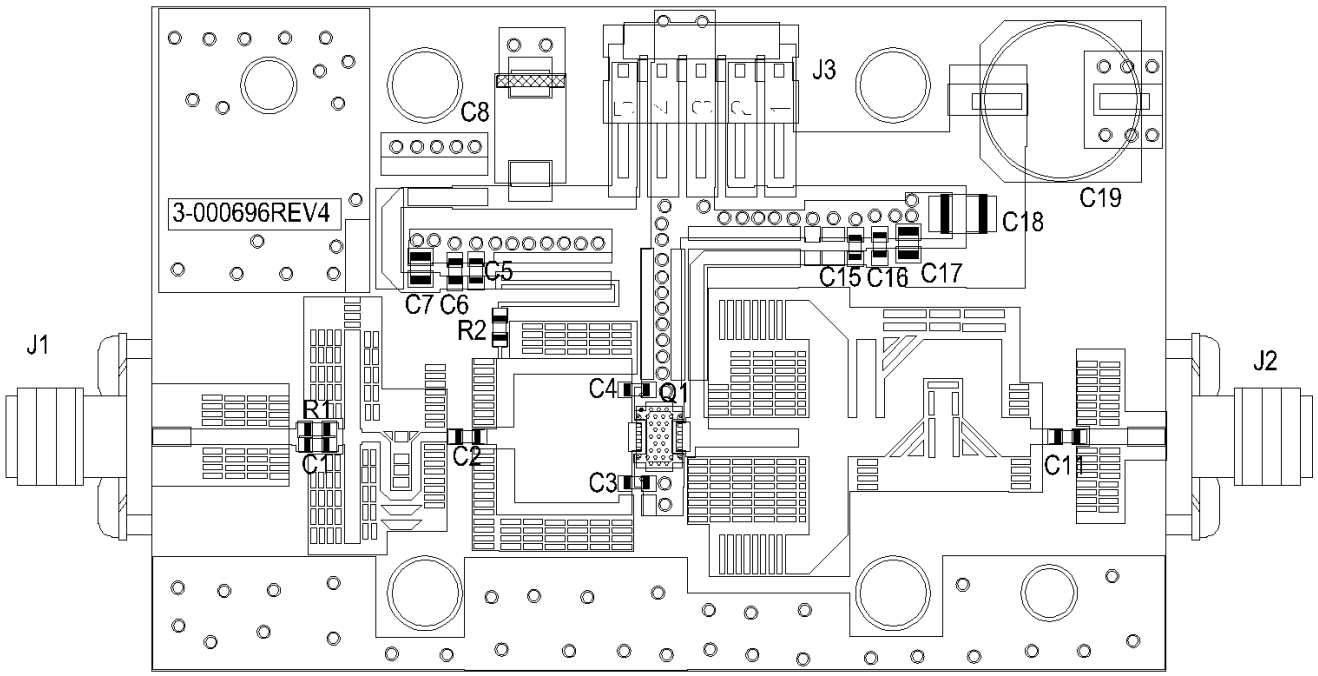
CGHV27030S -AMP1 Application Circuit



CGHV27030S-AMP1 Application Circuit Schematic, 50 V



CGHV27030S-AMP1 Application Circuit Outline, 50 V



Electrical Characteristics When Tested in CGHV27030S-AMP2, 28 V, 2.5 - 2.7 GHz

Parameter	2.5 GHz	2.6 GHz	2.7 GHz	Units
Small Signal Gain	15.5	15.7	16.0	dB
Adjacent Channel Power @ P_{AVE} = 3.2 W	-42.0	-41.7	-41.2	dBc
Drain Efficiency @ P_{AVE} = 3.2 W	33.5	34.2	34.1	%
Input Return Loss	-9.0	-8.8	-10.2	dB

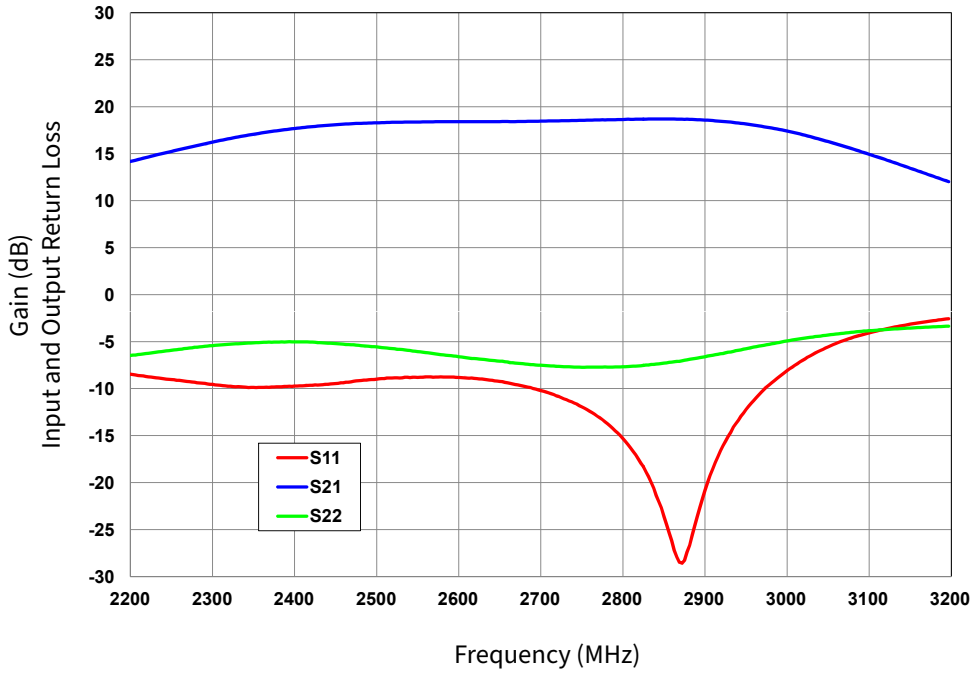


Figure 4. Small Signal Gain and Return Losses vs Frequency
V_{DD} = 28 V, I_{DQ} = 0.13 A

Typical Performance in Application Circuit CGHV27030S-AMP2

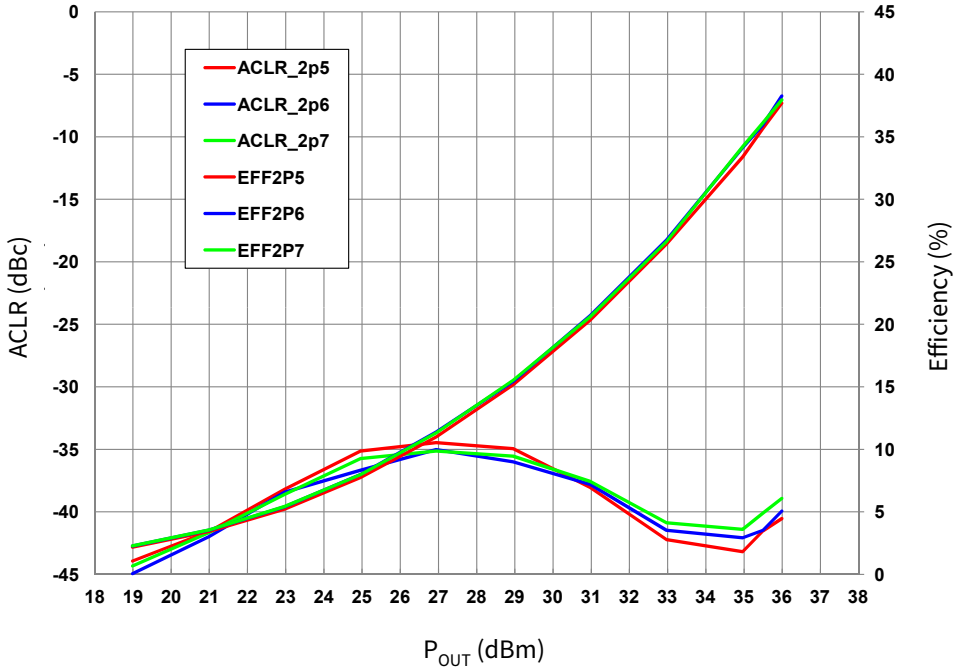


Figure 5. Typical Drain Efficiency and ACLR vs. Output Power
V_{DD} = 28 V, I_{DQ} = 0.13 A, 1c WCDMA, PAR = 7.5 dB

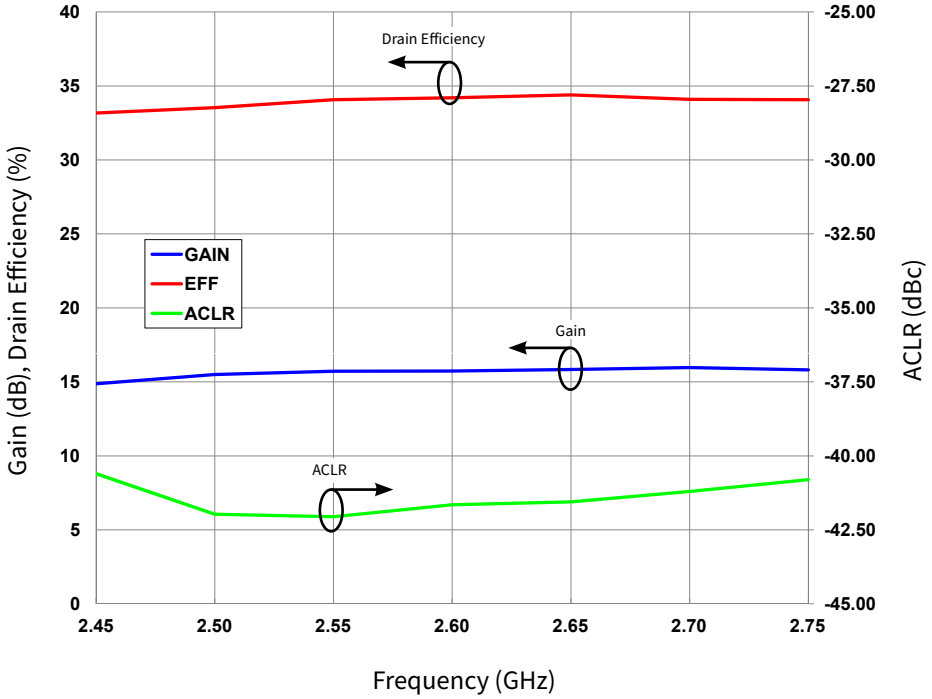
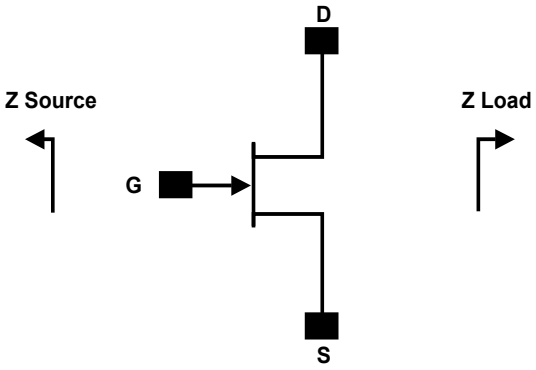


Figure 6. Typical Gain, Drain Efficiency and ACLR vs Frequency
V_{DD} = 28 V, I_{DQ} = 0.13 A, P_{AVE} = 3.2 W, 1c WCDMA, PAR = 7.5 dB

Source and Load Impedances for Application Circuit CGHV27030S-AMP2



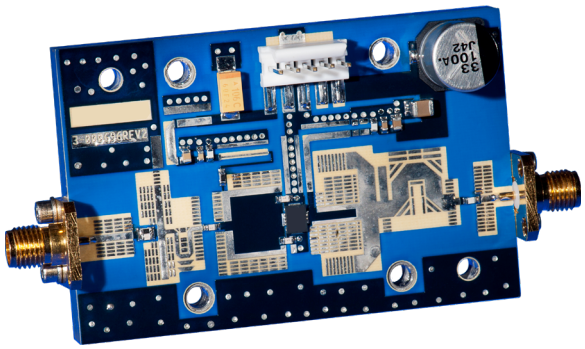
Frequency (MHz)	Z Source	Z Load
2500	2.9 - j2.7	14.5 + j7.4
2600	3.1 - j2.9	13.8 + j7.3
2700	2.7 - j3.1	12.9+j7.6

Notes:
[1] V_{DD} = 28 V, I_{DQ} = 0.13 A in the DFN package
[2] Impedances are extracted from the CGHV27030S-AMP2 application circuit and are not source and load pull data derived from the transistor

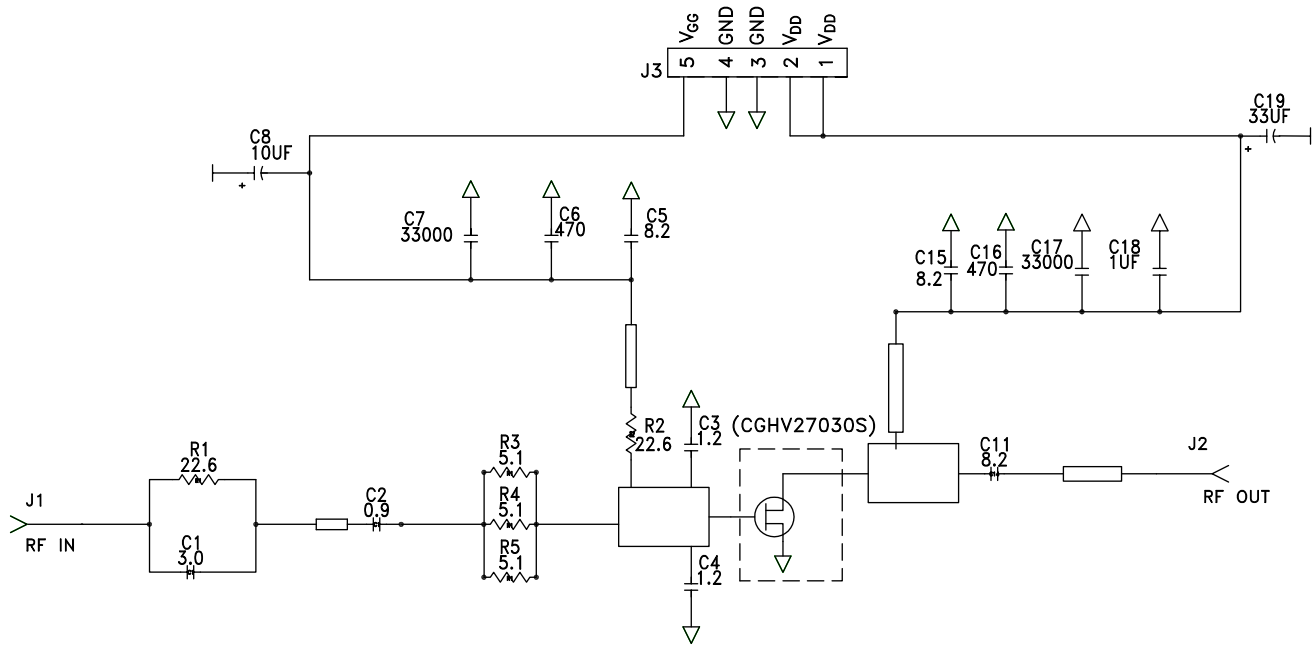
CGHV27030S-AMP2 Bill of Materials

Designator	Description	Qty
R1, R2	RES, 22.6 ohm, +/-1%, 1/16W, 0603	2
C1	CAP, 3.0 pF, ±0.1 pF, 0603, ATC	1
C2	CAP, 0.9 pF, ±0.05 pF, 0603, ATC	3
R3, R4, R5	RES, 1/16W, 0603, 1%, 5.1% ohms	3
C3,C4	CAP, 1.2 pF, +/-0.1 pF, 0603, ATC	2
C5, C11, C15	CAP, 8.2 pF, ±0.25 pF, 0603, ATC	3
C6, C16	CAP, 470 pF, 5%, 100 V, 0603	2
C7, C17	CAP, 33000 pF, 0805, 100 V, 0603, X7R	2
C18	CAP, 1.0 µF, 100 V, 10%, X7R, 1210	1
C8	CAP, 10 µF, 16 V TANTALUM	1
C19	CAP, 33 µF, 20%, G CASE	1
J1, J2	CONN, SMA, PANEL MOUNT JACK	2
J3	HEADER RT>PLZ .1CEN LK 5 POS	1
PCB	PCB, ROGERS 4350, ER 3.66	1
Q1	CGHV27030S, QFN	1

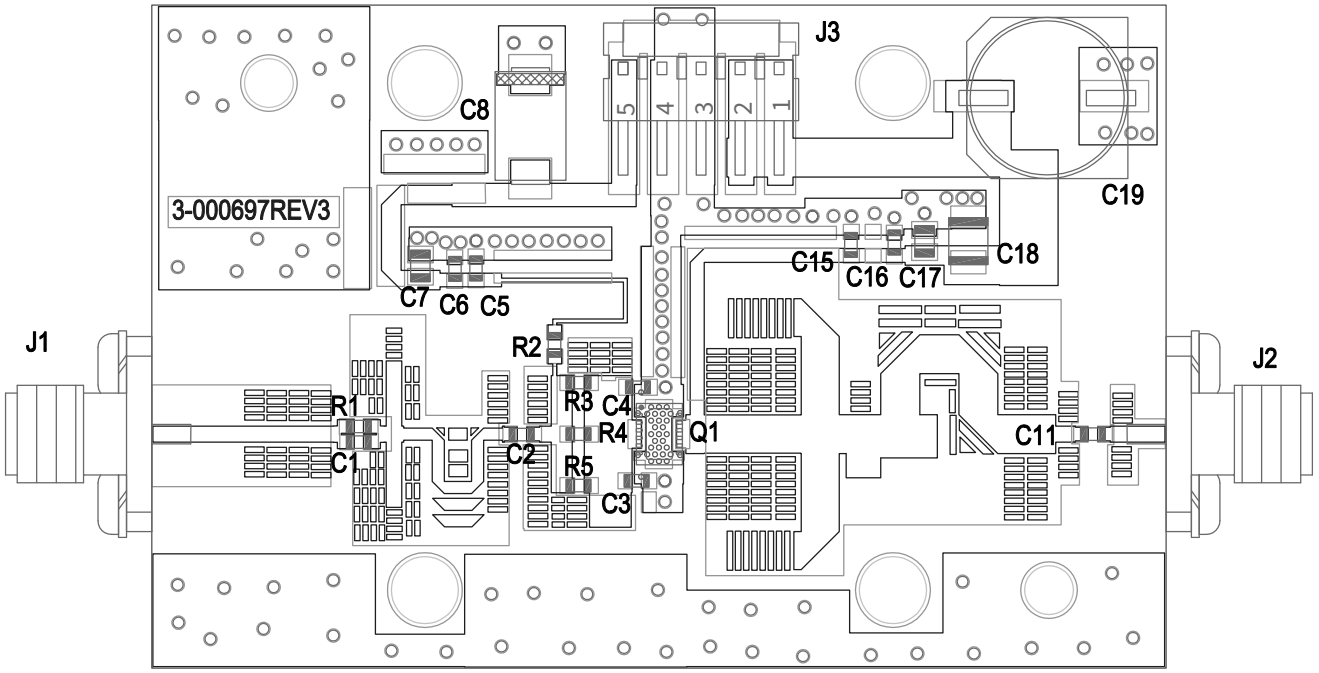
CGHV27030S-AMP2 Application Circuit



CGHV27030S-AMP2 Application Circuit Schematic, 28 V



CGHV27030S-AMP2 Application Circuit Outline, 28 V



Electrical Characteristics When Tested in CGHV27030S-AMP3, 28 V, 1.8 - 2.2 GHz

Parameter	1.8 GHz	2.0 GHz	2.2 GHz	Units
Small Signal Gain	19	19	18	dB
Adjacent Channel Power @ P_{AVE} = 3.2 W	-37	-38	-39	dBc
Drain Efficiency @ P_{AVE} = 3.2 W	35	35	33	%
Input Return Loss	5	6	7	dB

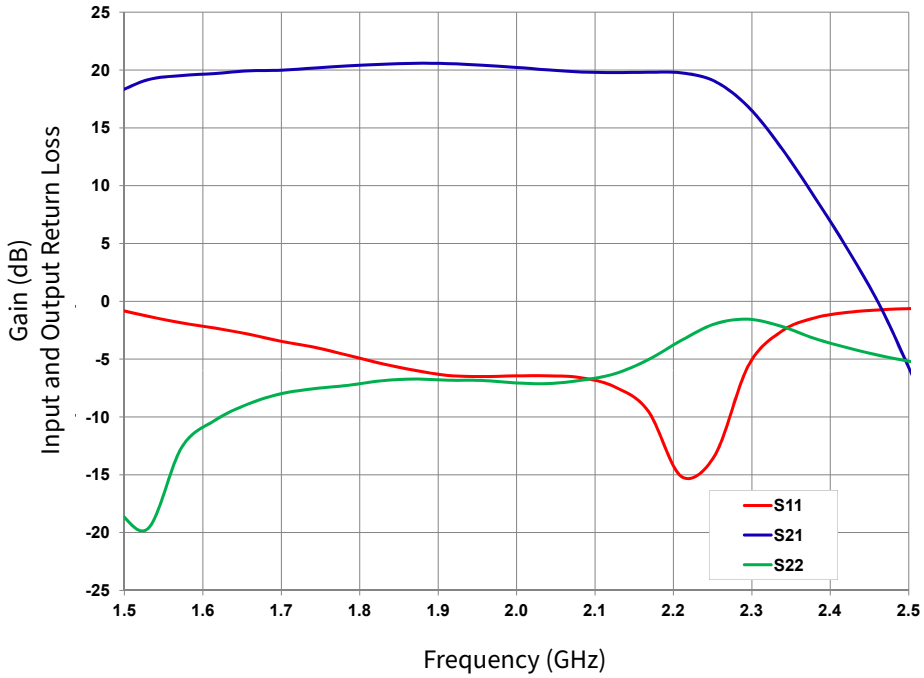


Figure 7. Small Signal Gain and Return Losses vs Frequency
V_{DD} = 28 V, I_{DQ} = 0.13 A

Typical Performance in Application Circuit CGHV27030S-AMP3

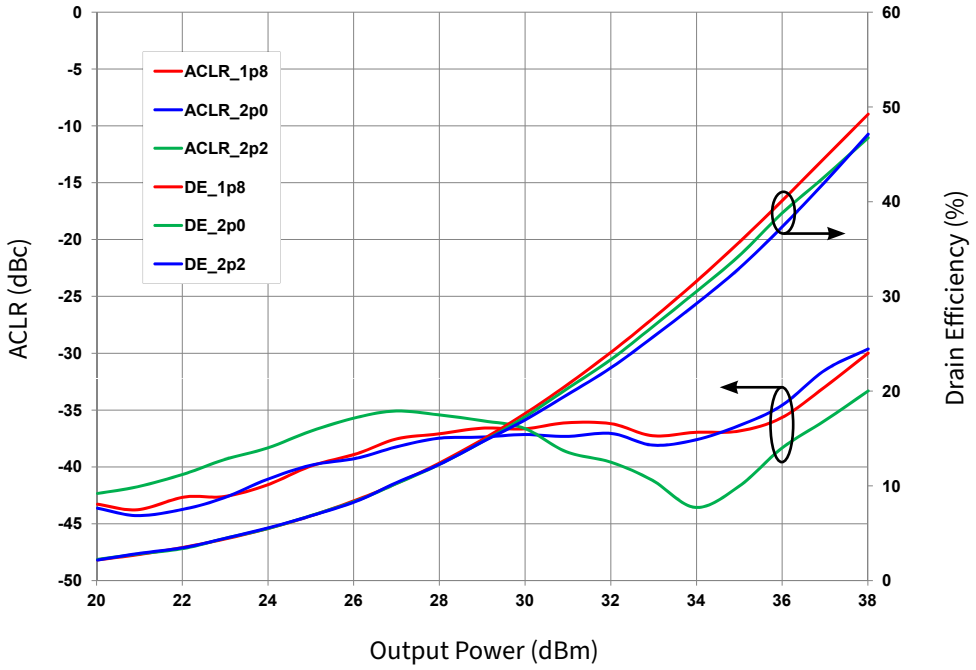


Figure 8. Typical Drain Efficiency and ACLR vs. Output Power
V_{DD} = 28 V, I_{DQ} = 0.13 A, 1c WCDMA, PAR = 7.5 dB

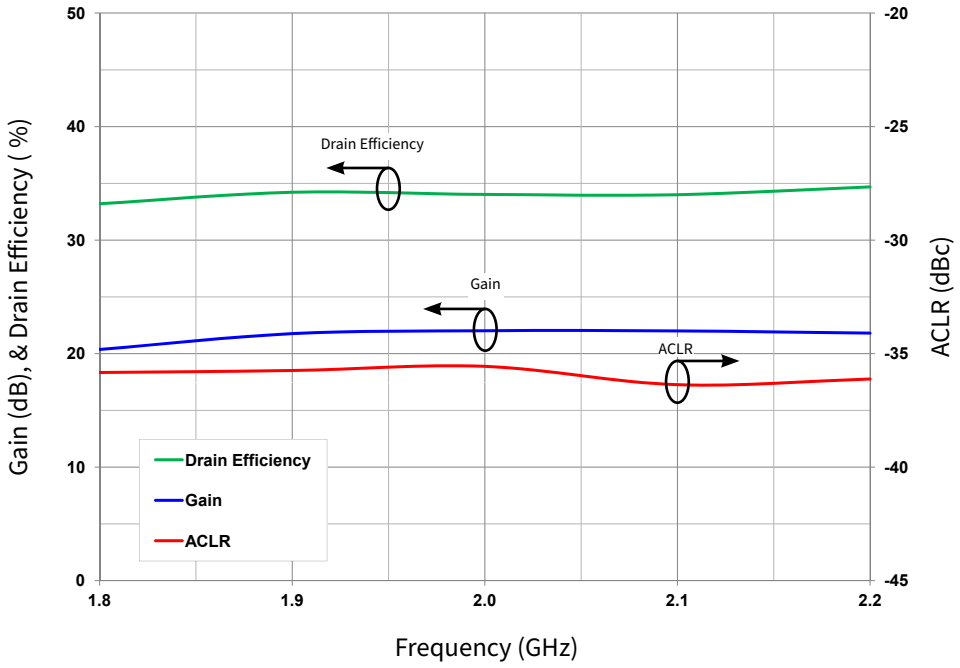
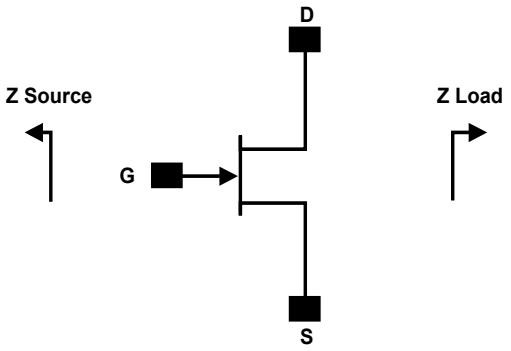


Figure 9. Typical Gain, Drain Efficiency and ACLR vs Frequency
V_{DD} = 28 V, I_{DQ} = 0.13 A, P_{AVE} = 3.2 W, 1c WCDMA, PAR = 7.5 dB

Source and Load Impedances for Application Circuit CGHV27030S-AMP3



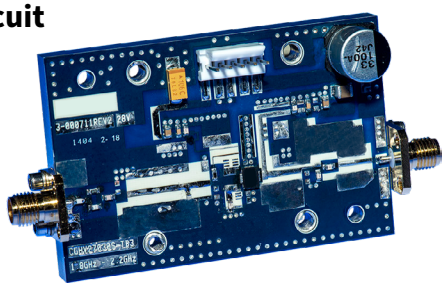
Frequency (MHz)	Z Source	Z Load
1800	6.16 - j3.5	21.9 + j6.5
2000	6.8 - j1.7	21 + j8.4
2200	5.5 - j2.0	20.8 + j11

Notes:
[1] V_{DD} = 28 V, I_{DQ} = 0.13 A in the DFN package
[2] Impedances are extracted from the CGHV27030S-AMP3 application circuit and are not source and load pull data derived from the transistor

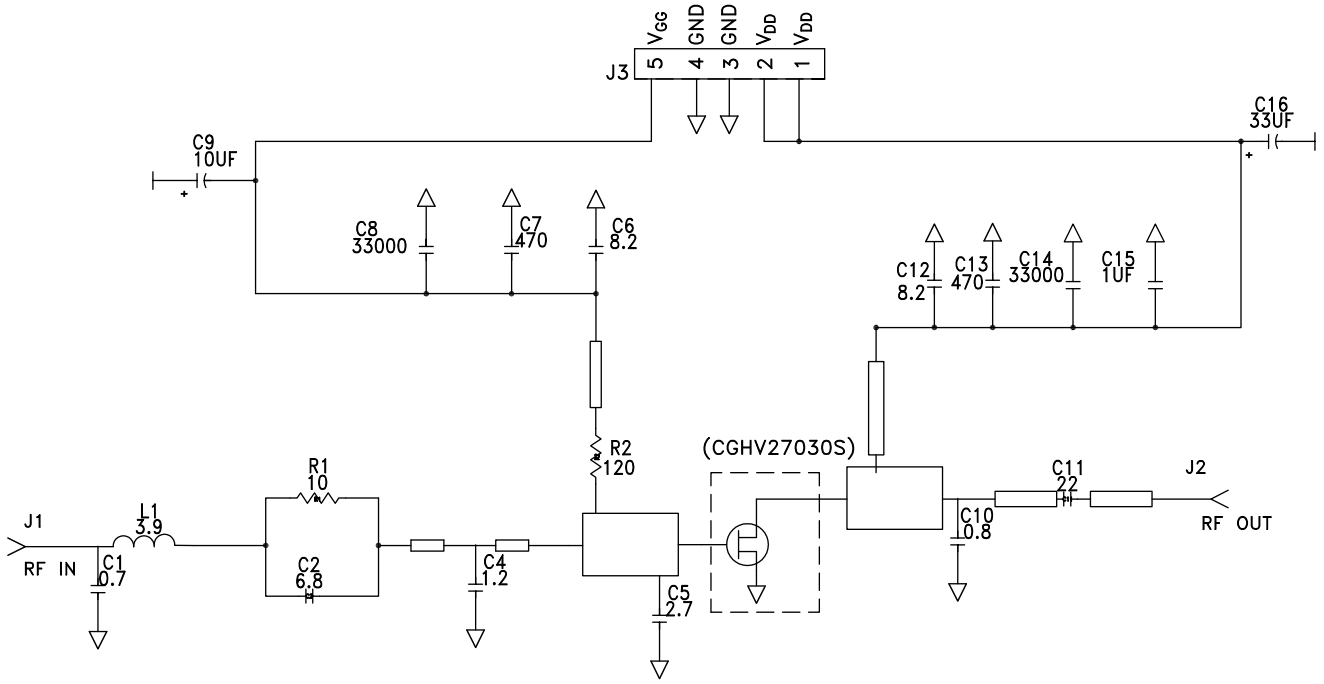
CGHV27030S-AMP3 Bill of Materials

Designator	Description	Qty
R1	RES, 10 ohm, +/-1%, 1/16W, 0603	1
R2	RES, 120 ohm, +/-1%, 1/16W, 0603	1
L1	IND, 3.9 nH, +/-5%, 0603, JOHANSON	1
C1	CAP, 0.7 pF, +/-0.1 pF, 0603, ATC	1
C2	CAP, 6.8 pF, +/-5%, 0603, ATC	1
C3	CAP, 47 pF, +/-0.1 pF, 0603, ATC	1
C4	CAP, 1.5 pF, +/-0.1 pF, 0603, ATC	1
C5	CAP, 2.7 pF, +/-0.1 pF, 0603, ATC	1
C6, C12	CAP, 8.2 pF, +/-0.25 pF, 0603, ATC	2
C7, C13	CAP, 470 pF, 5%, 100 V, 0603	2
C8, C14	CAP, 33000 pF, 0805, X7R	2
C9	CAP, 10 µF, 16 V, TANTALUM	1
C10	CAP, 0.7 pF, +/-0.05 pF, 0603, ATC	1
C11	CAP, 20 pF, +/-5%, 0603, ATC	1
C15	CAP, 1.0 µF, 100V, 10%, X7R, 1210	1
C16	CAP, 33 µF, 20%, G CASE	1
J1, J2	CONN, SMA, PANEL MOUNT JACK, FLANGE, 4-HOLE, BLUNT POST	2
	PCB, RO4350, 0.020" THK	1
	BASEPLATE, CGH35015, 2.60 X 1.7	1
J3	HEADER RT>PLZ .1CEN LK 5POS	1
	2-56 SOC HD SCREW 1/4 SS	4
	#2 SPLIT LOCKWASHER SS	4
Q1	CGHV27030S, QFN	1

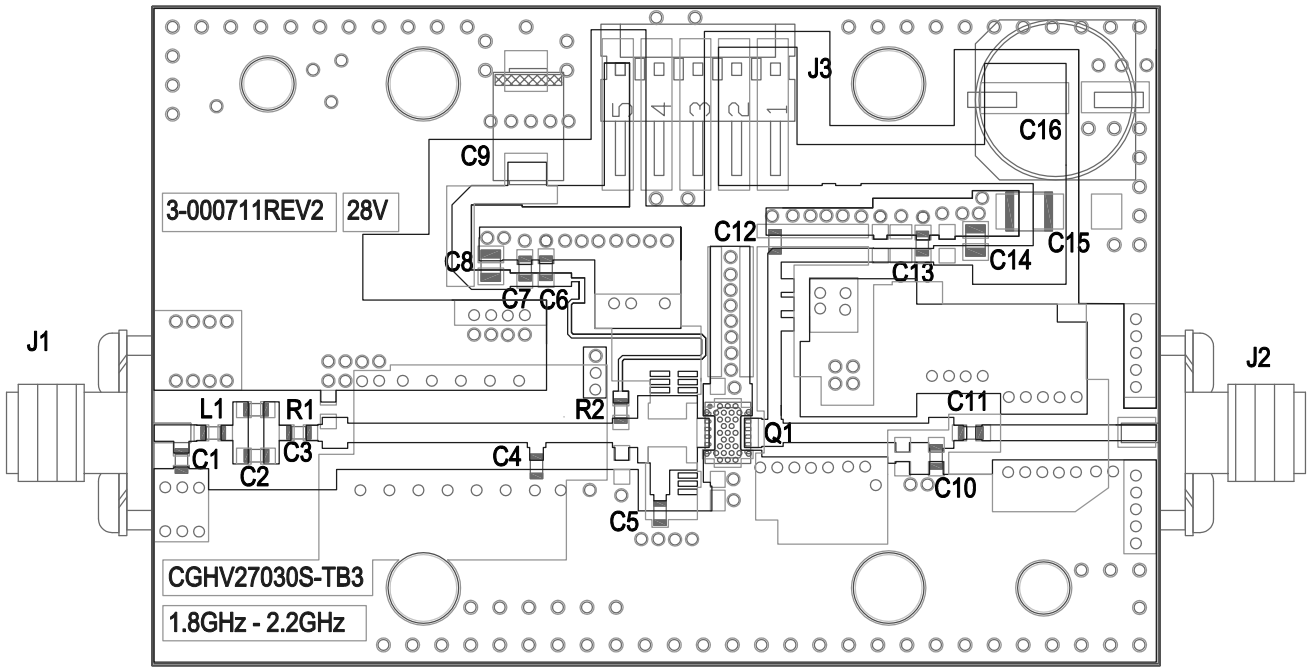
CGHV27030S-AMP3 Application Circuit



CGHV27030S-AMP3 Application Circuit Schematic, 28 V



CGHV27030S-AMP3 Application Circuit Outline, 28 V



Electrical Characteristics When Tested in CGHV27030S-AMP3, 28 V, 1.8 - 2.2 GHz

Parameter	1.8 GHz	2.0 GHz	2.2 GHz	Units
Small Signal Gain	22	22	21	dB
Adjacent Channel Power @ P_{AVE} =5 W	-39	-38	-37	dBc
Drain Efficiency @ P_{AVE} = 5 W	31	31	33	%
Input Return Loss	5	7	6	dB

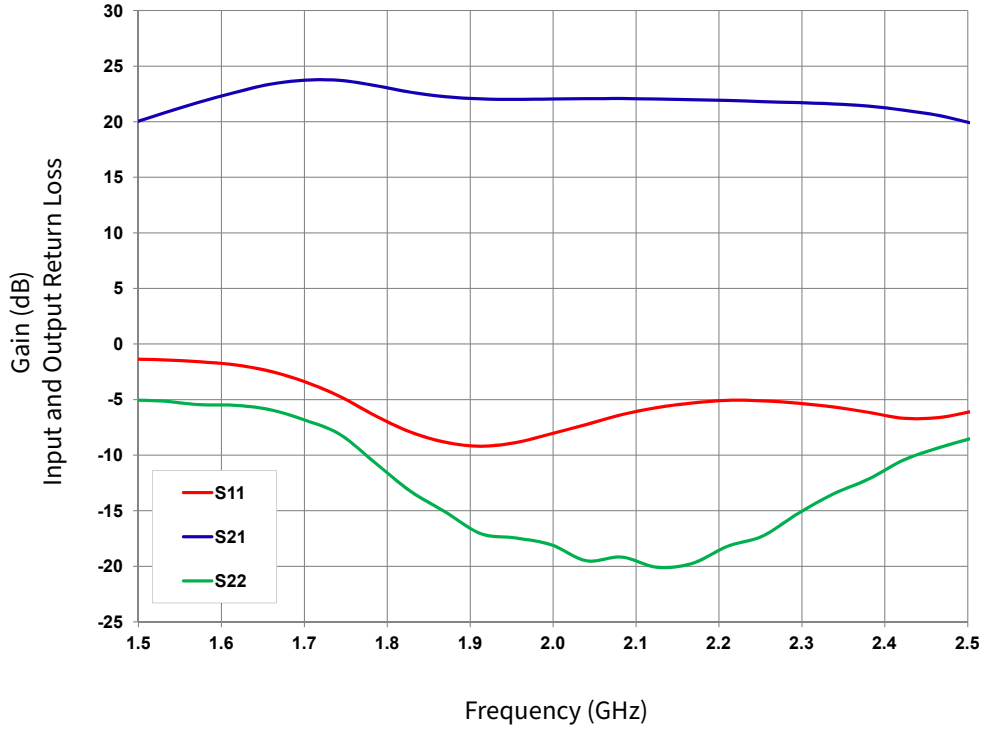


Figure 10. Small Signal Gain and Return Losses vs Frequency
V_{DD} = 50 V, I_{DQ} = 0.13 A

Typical Performance in Application Circuit CGHV27030S-AMP4

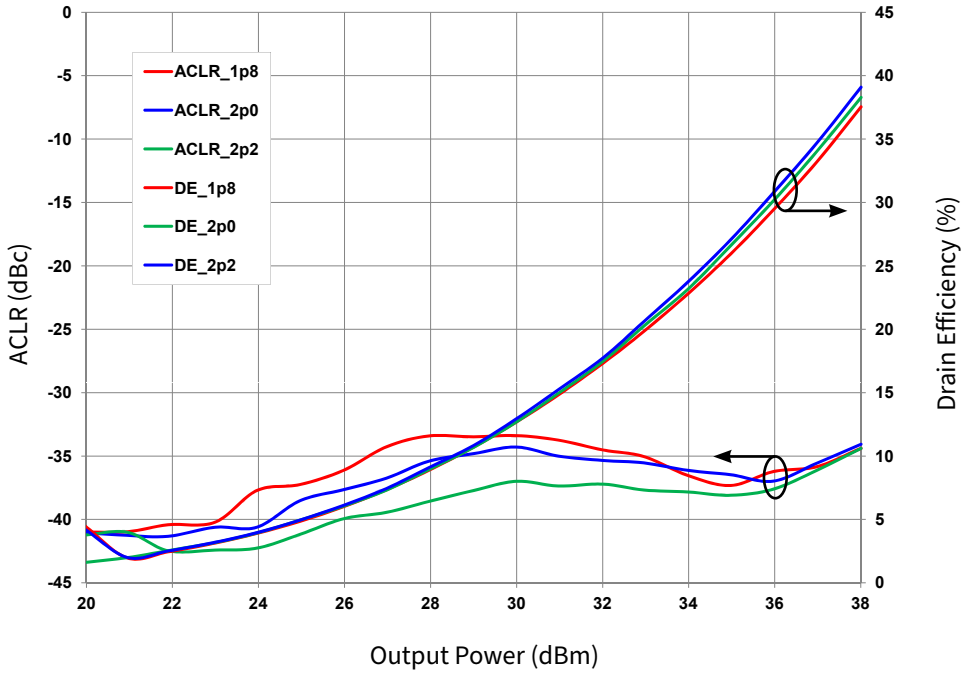


Figure 11. Typical Drain Efficiency and ACLR vs. Output Power
V_{DD} = 50 V, I_{DQ} = 0.13 A, 1c WCDMA, PAR = 7.5 dB

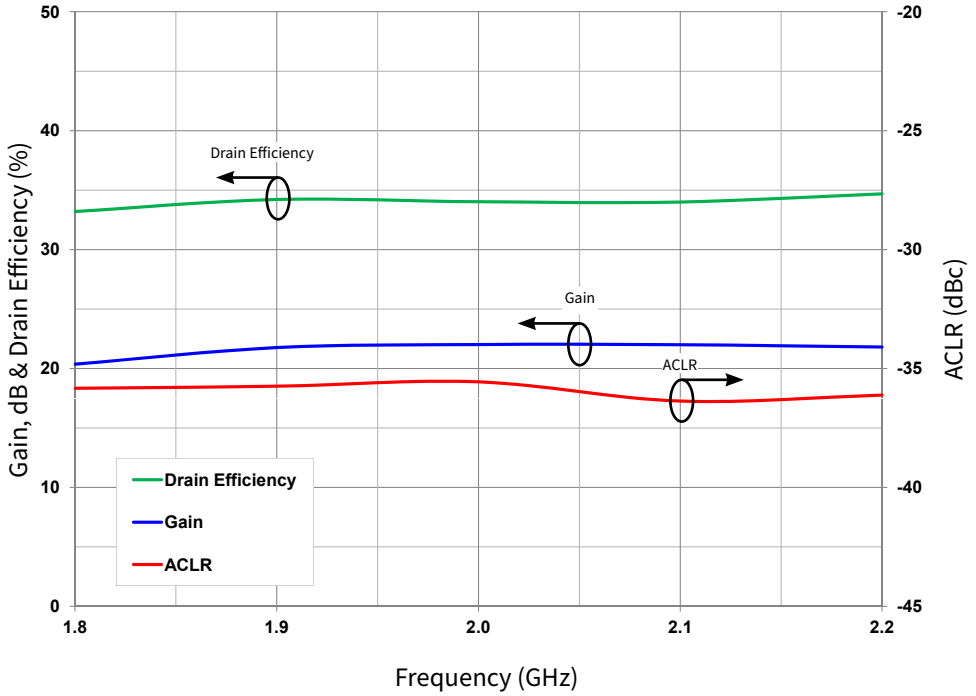
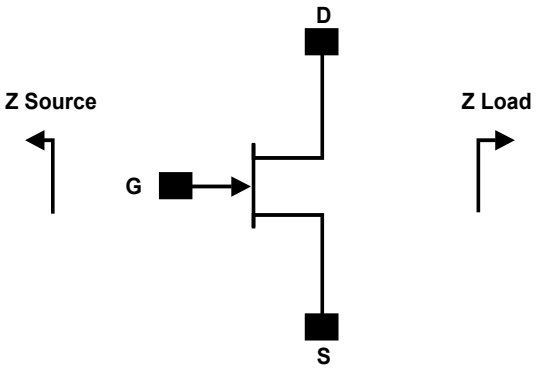


Figure 12. Typical Gain, Drain Efficiency and ACLR vs Frequency
V_{DD} = 50 V, I_{DQ} = 0.13 A, P_{AVE} = 5 W, 1c WCDMA, PAR = 7.5 dB

Source and Load Impedances for Application Circuit CGHV27030S-AMP4



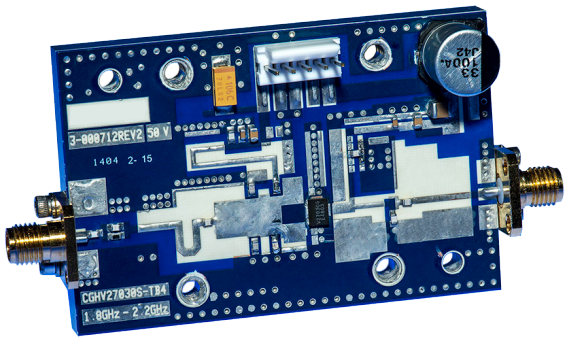
Frequency (MHz)	Z Source	Z Load
1800	5.0 - j3.3	20.0 + j18.6
2000	6.4 - j3.3	17.8 + j19.1
2200	4.0 - j2.7	16.2 + j20.8

Notes:
[1] V_{DD} = 50 V, I_{DQ} = 0.13 A in the DFN package
[2] Impedances are extracted from the CGHV27030S-AMP4 application circuit and are not source and load pull data derived from the transistor

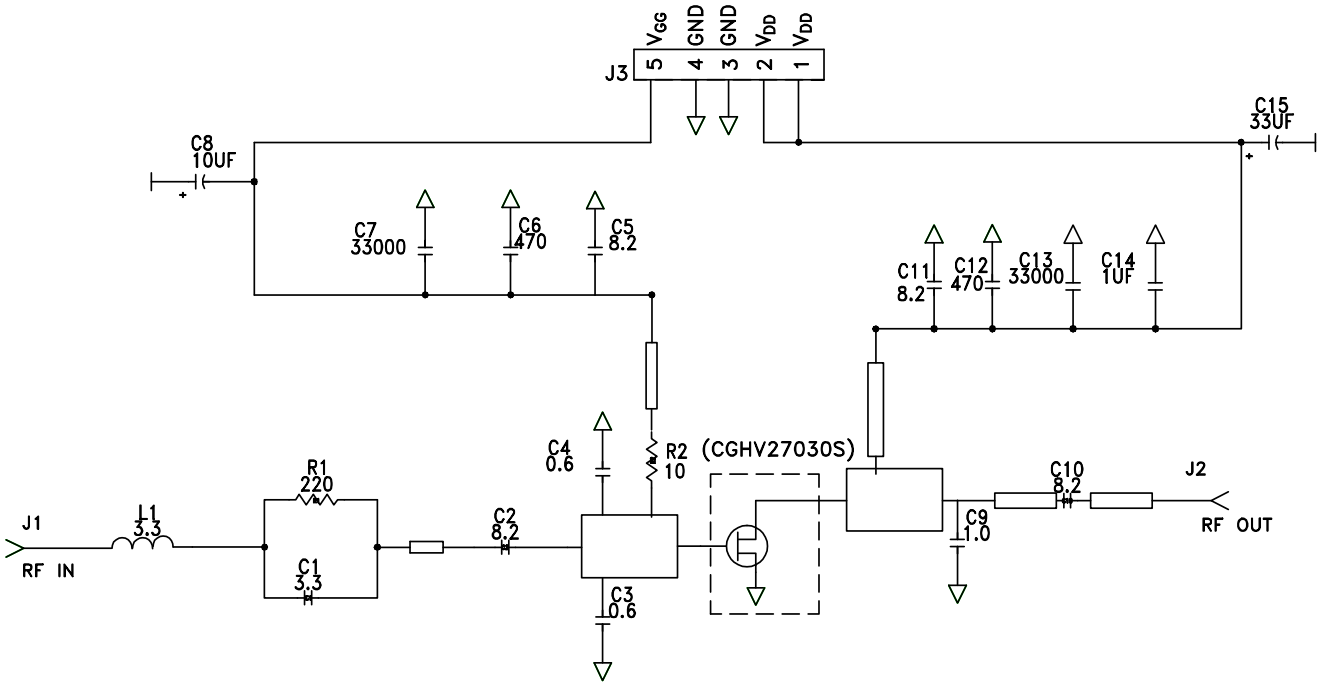
CGHV27030S-AMP4 Bill of Materials

Designator	Description	Qty
R1	RES, 220 ohm, +/-1%, 1/16W, 0603	1
R2	RES, 10 ohm, +/-1%, 1/16W, 0603	1
L1	IND, 3.3 nH, +/-5%, 0603, JOHANSON	1
C1	CAP, 3.3 pF, +/-0.1 pF, 0603, ATC	1
C2, C5, C10, C11	CAP, 8.2 pF, +/-5%, 0603, ATC	1
C3, C4	CAP, 0.6 pF, +/-0.1 pF, 0603, ATC	2
C6, C12	CAP, 470 pF, 5%, 100V, 0603, X	2
C7, C13	CAP, 33000 pF, 0805, 100V, X7R	2
C8	CAP, 10 µF, 16 V, TANTALUM	1
C9	CAP, 1.0 pF, +/-0.1 pF, 0603, ATC	1
C14	CAP, 1.0 µF, 100V, 10%, X7R, 1210	1
C15	CAP, 33 µF, 20%, G CASE	1
J1, J2	CONN, SMA, PANEL MOUNT JACK, FLANGE, 4-HOLE, BLUNT POST	2
PCB	PCB, RO4350, 0.020” THK	1
J3	HEADER RT>PLZ .1CEN LK 5POS	1
Q1	CGHV27030S, QFN	1

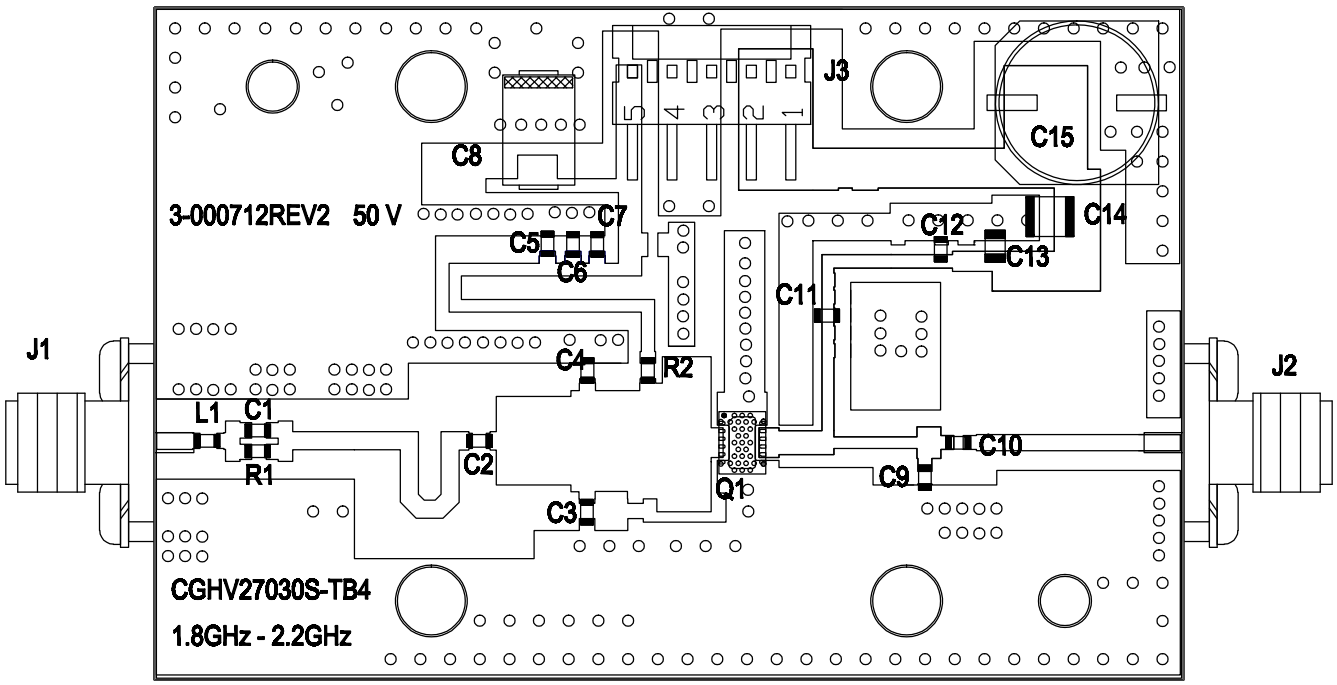
CGHV27030S-AMP4 Application Circuit



CGHV27030S-AMP4 Application Circuit Schematic, 50 V



CGHV27030S-AMP4 Application Circuit Outline, 50 V



Electrical Characteristics When Tested in CGHV27030S-AMP5, 50 V, 1.2 - 1.4 GHz

Parameter	1.2 GHz	1.3 GHz	1.4 GHz	Units
Output Power @ P_{IN} = 27 dBm	35.5	33.5	32.5	W
Gain @ P_{IN} = 27 dBm	18.5	18.25	18.1	dB
Drain Efficiency @ P_{IN} = 27 dBm	71	67	65	%

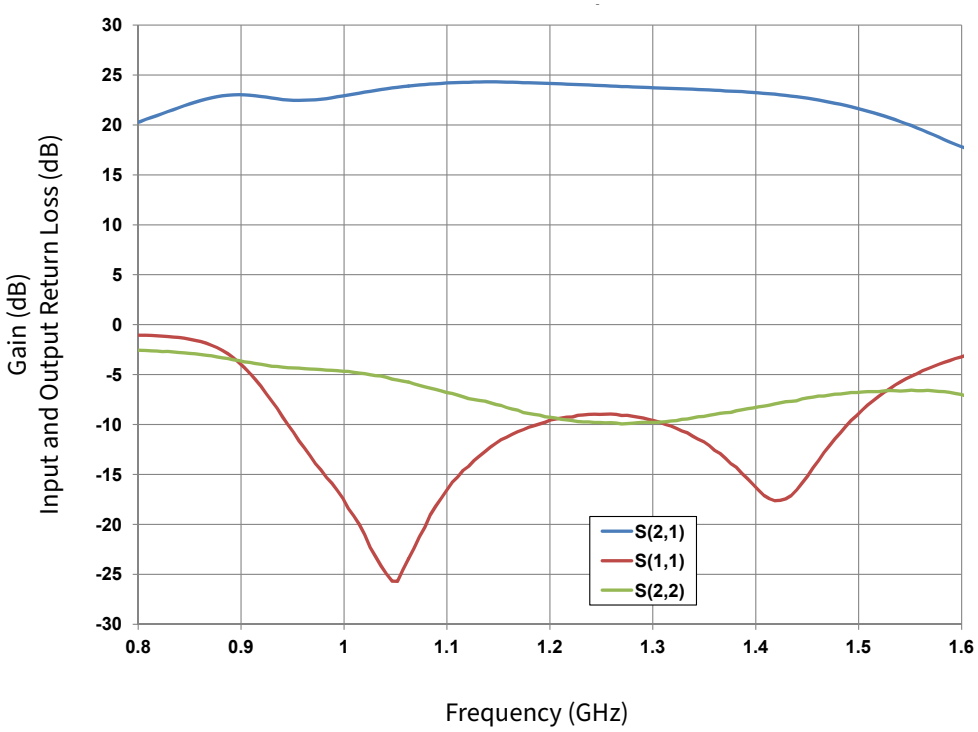


Figure 13. Small Signal Gain and Return Losses vs Frequency
V_{DD} = 50 V, I_{DQ} = 0.125 A

Typical Performance in Application Circuit CGHV27030S-AMP5

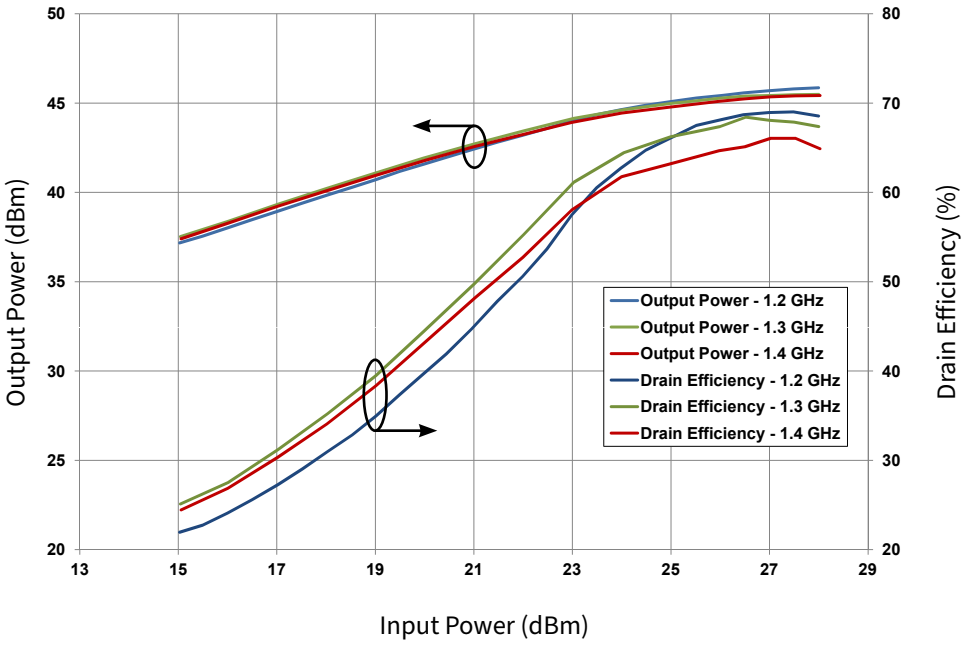


Figure 14. Typical Output Power and Drain Efficiency Input Power
V_{DD} = 50 V, I_{DQ} = 0.125 A, Pulse Width = 100 us, Duty Cycle = 10%

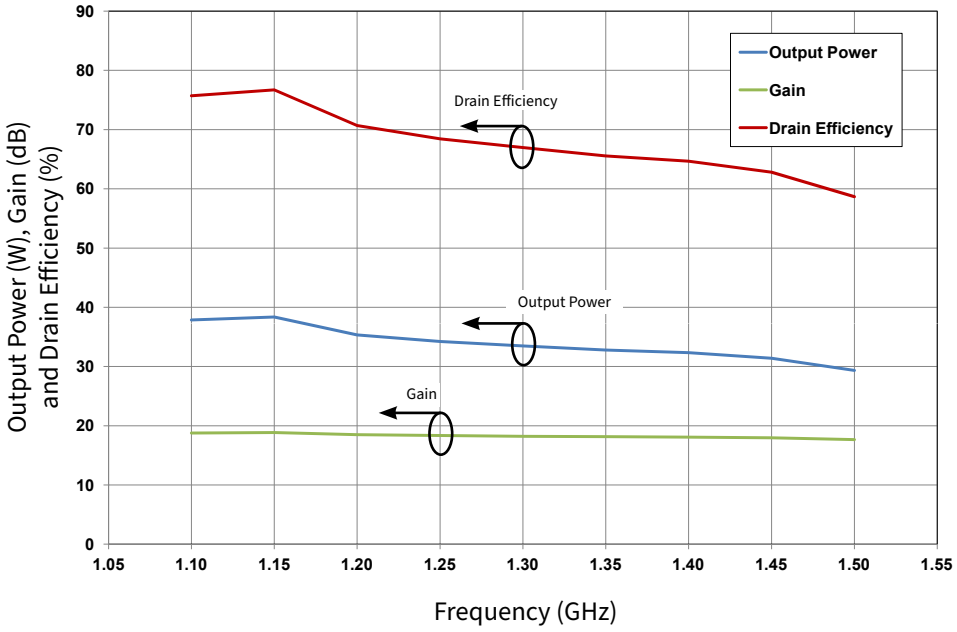
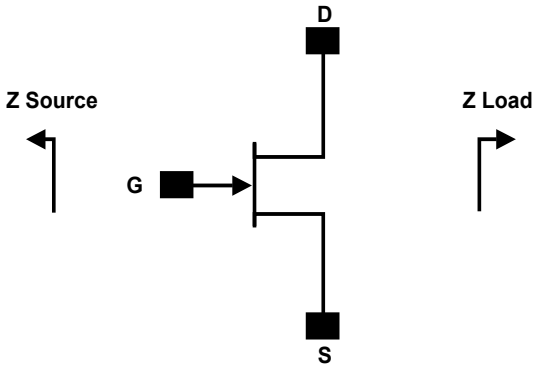


Figure 15. Typical Output Power, Gain, and Drain Efficiency vs Frequency
V_{DD} = 50 V, I_{DQ} = 0.125 A, P_{IN} = 27 dBm, Pulse Width = 100 us, Duty Cycle = 10%

Source and Load Impedances for Application Circuit CGHV27030S-AMP5



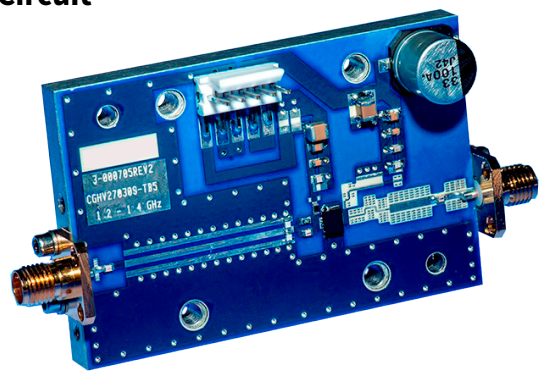
Frequency (MHz)	Z Source	Z Load
1200	8.6 + j5.4	25.4 + j29.2
1300	8.7 + j5.1	27.6 + j30.5
1400	7.4 + j5.2	30.1 + j31.8

Notes:
[1] V_{DD} = 50 V, I_{DQ} = 0.125 A in the DFN package
[2] Impedances are extracted from the CGHV27030S-AMP5 application circuit and are not source and load pull data derived from the transistor

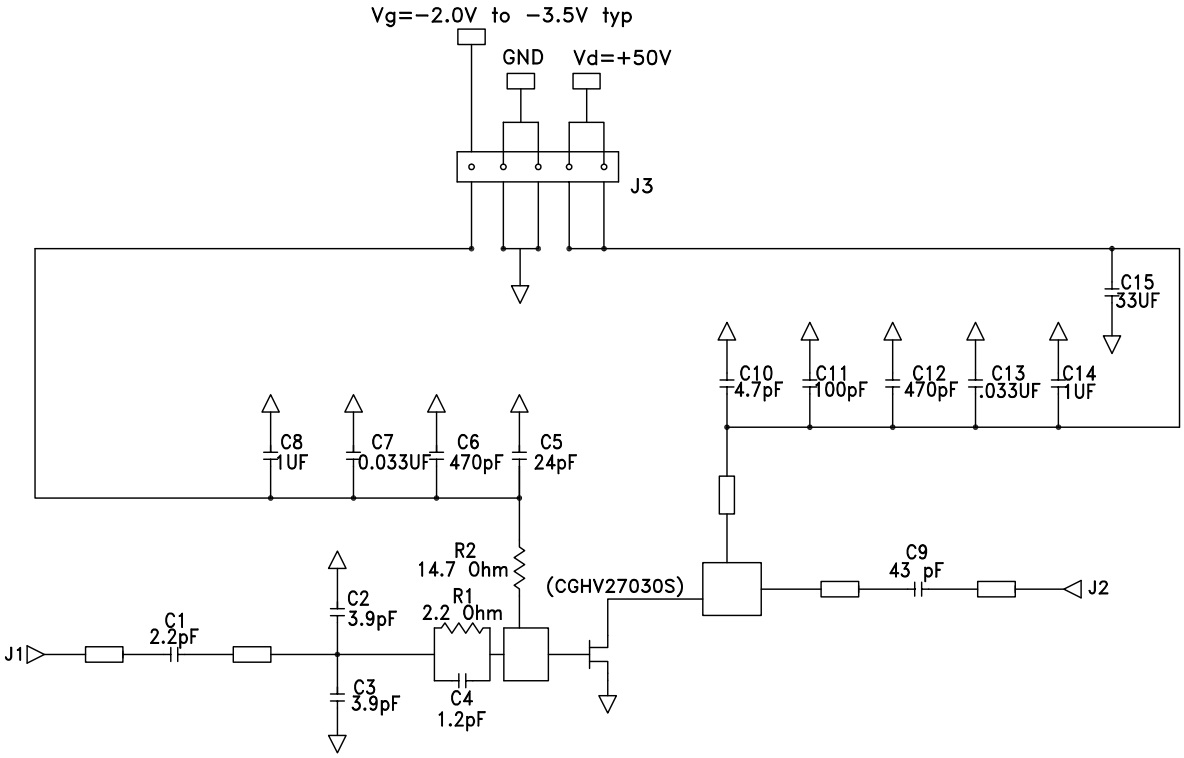
CGHV27030S-AMP5 Bill of Materials

Designator	Description	Qty
R1	RES, 2.2 ohm, 1/10W 5% 0603 SMD	1
R2	RES, 1/16W, 0603, 1%, 14.7 ohms	1
C1	CAP, 2.2 pF, +/-0.1 pF, 0603, ATC	1
C2, C3	CAP, 3.9 pF, +/-0.1 pF, 0603, ATC	2
C4	CAP, 1.2 pF, +/-0.1 pF, 0603, ATC	1
C5	CAP, 24 pF, +/-5%, 0603, ATC	1
C6, C12	CAP, 470 pF, 5%, 100V, 0603, X	2
C7, C13	CAP, 33000 pF, 0805, 100V, Z7R	2
C8, C14	CAP, 1.0 µF, 100V, 10%, X7R, 1210	2
C9	CAP, 43 pF, +/-5%, 0603, ATC	1
C10	CAP, 4.7 pF, +/-0.1 pF, 0603, ATC 600S	1
C11	CAP, 100.0 pF, +/-5%, 0603, ATC	1
C15	CAP, 33 µF, 20%, G CASE	
J1, J2	CONN, SMA, PANEL MOUNT JACK, FLANGE, 4-HOLE, BLUNT POST	2
PCB	PCB, RO4350, L-BAND, 1.7" X 2.6"	1
J3	HEADER RT>PLZ .1CEN LK 5POS	1
Q1	CGHV27030S, QFN	1

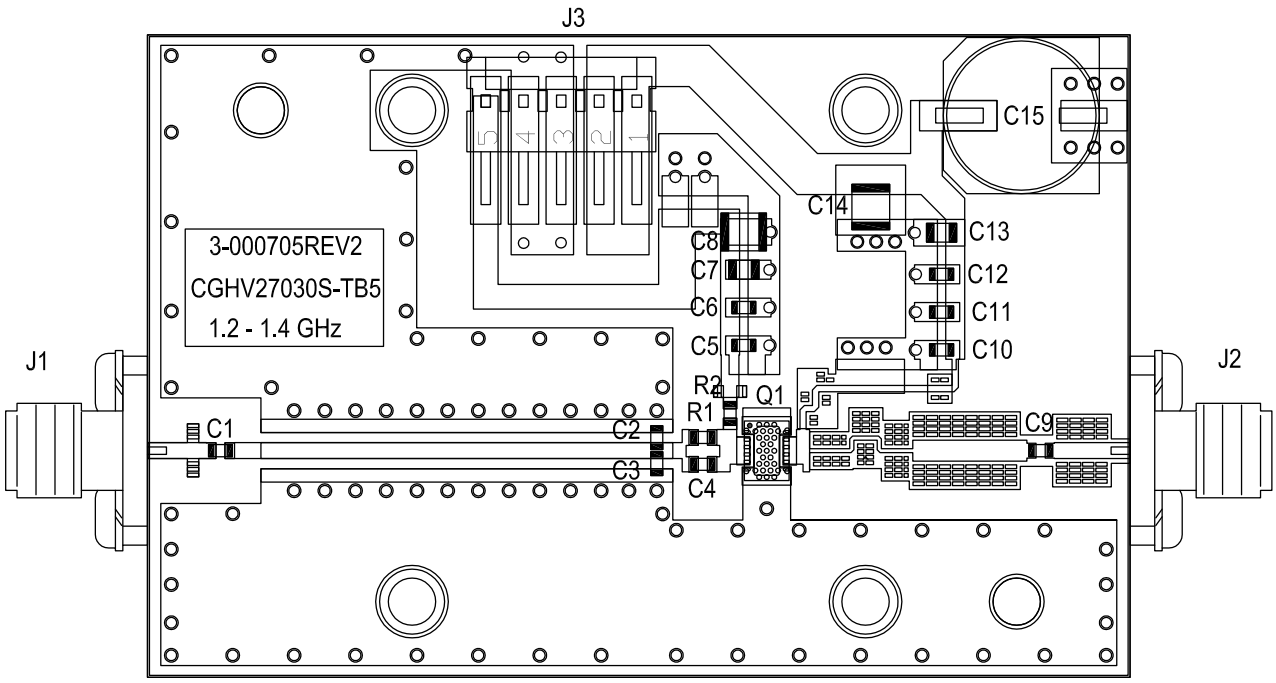
CGHV27030S-AMP5 Application Circuit



CGHV27030S-AMP5 Application Circuit Schematic, 50 V



CGHV27030S-AMP5 Application Circuit Outline, 50 V



Electrostatic Discharge (ESD) Classifications

Parameter	Symbol	Class	Classification Level	Test Methodology
Human Body Model	HBM	1A		JEDEC JESD22 A114-D
Charge Device Model	CDM	0CB		JEDEC JESD22 C101-C

Moisture Sensitivity Level (MSL) Classification

Parameter	Symbol	Level	Test Methodology
Moisture Sensitivity Level	MSL	3 (168 hours)	IPC/JEDEC J-STD-20

Typical Performance

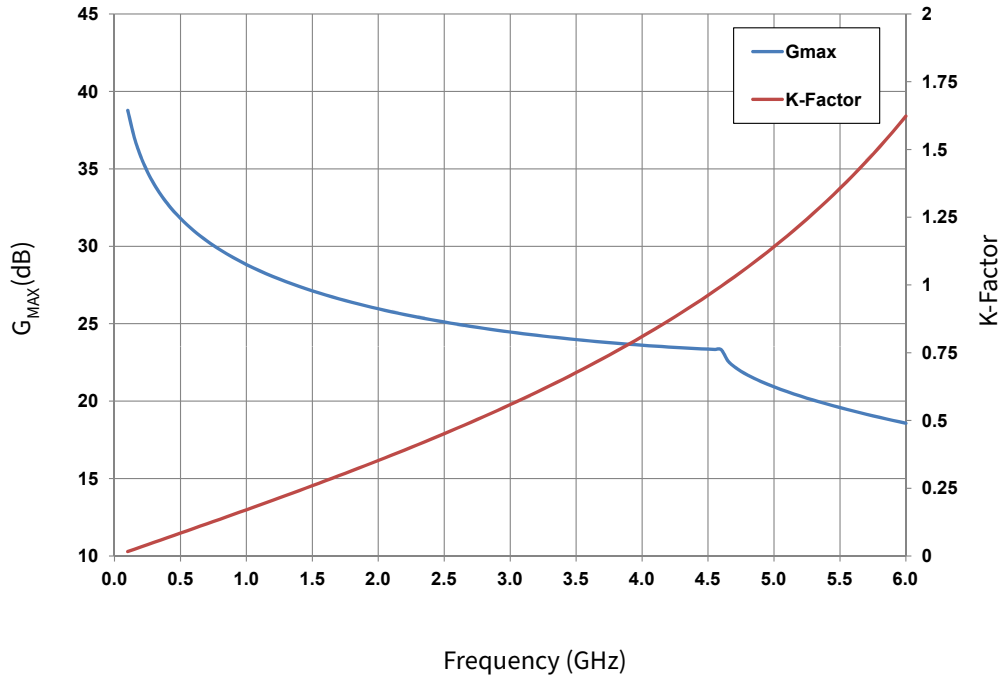
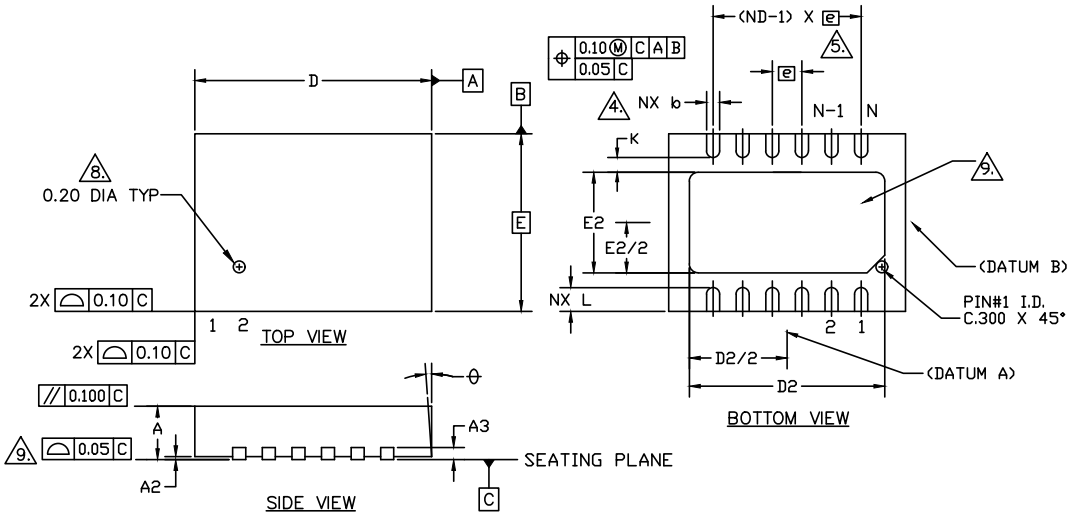


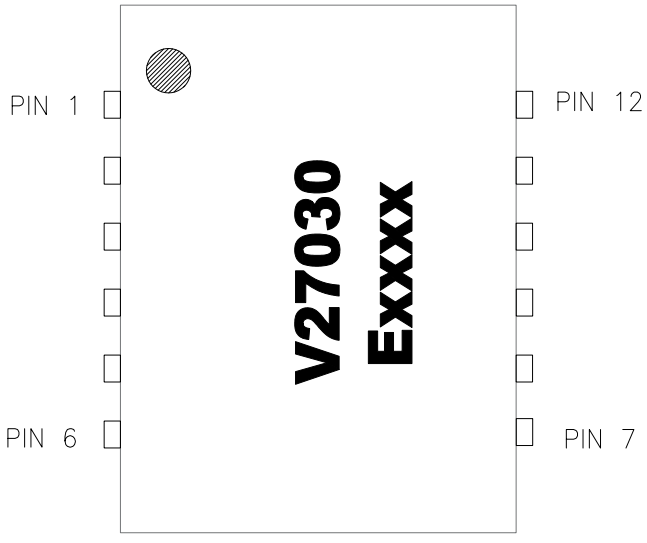
Figure 16. G_{MAX} and K-Factor vs Frequency
V_{DD} = 50 V, I_{DQ} = 130 mA, T_{CASE} = 25°C

Product Dimensions CGHV27030S (Package 3 x 4 DFN)

SYMBOL	COMMON DIMENSIONS			NOTE
	MIN.	NOM.	MAX.	
A	0.80	0.90	1.0	
A1	0.00	0.02	0.05	
A3		0.203 REF.		
θ	0	——	12	2
D		4.00 BSC		
E		3.00 BSC		
e		0.50 BSC		
N		12		3
ND		6		5
L	0.35	0.40	0.45	
b	0.18	0.25	0.30	4
D2	3.20	3.30	3.40	
E2	1.60	1.7	1.80	
K	0.20	——	——	



PIN	Input/Output
1	GND
2	NC
3	RF IN
4	RF IN
5	NC
6	GND
7	GND
8	NC
9	RF OUT
10	RF OUT
11	NC
12	GND



Note: Leadframe finish for 3x4 DFN package is Nickel/Palladium/Gold. Gold is the outer layer

Part Number System

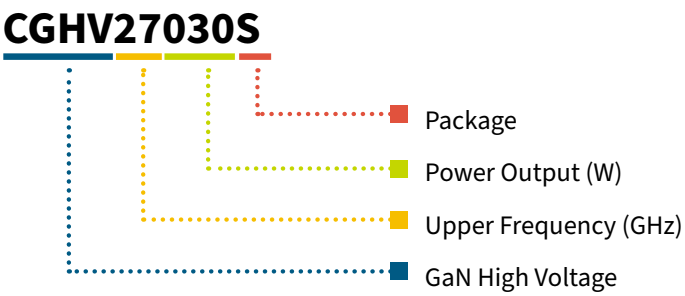


Table 1.

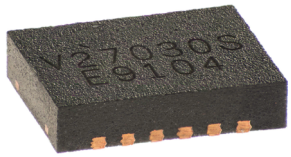
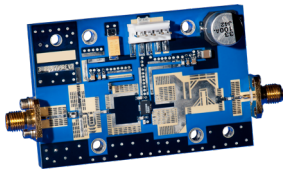
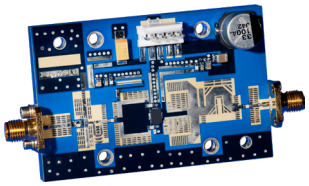
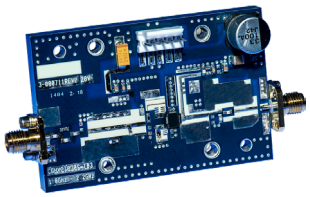
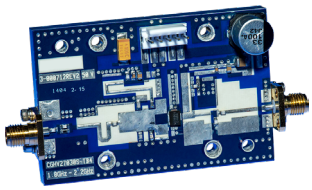
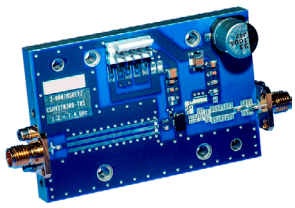
Parameter	Value	Units
Upper Frequency[1]	2.7	GHz
Power Output	30	W
Package	Surface Mount	—

Note:
[1] Alpha characters used in frequency code indicate a value greater than 9.9 GHz. See Table 2 for value.

Table 2.

Character Code	Code Value
A	0
B	1
C	2
D	3
E	4
F	5
G	6
H	7
J	8
K	9
Examples:	1A = 10.0 GHz 2H = 27.0 GHz

Product Ordering Information

Order Number	Description	Unit of Measure	Image
CGHV27030S	GaN HEMT	Each	
CGHV27030S-AMP1	Test board without GaN HEMT, 50 V 2.5-2.7 GHz	Each	
CGHV27030S-AMP2	Test board with GaN HEMT installed 28 V 2.5-2.7 GHz	Each	
CGHV27030S-AMP3	Test board with GaN HEMT installed 28 V 1.8-2.2 GHz	Each	
CGHV27030S-AMP4	Test board with GaN HEMT installed 50 V 1.8-2.2 GHz	Each	
CGHV27030S-AMP5	Test board with GaN HEMT installed 50 V 1.2-1.4 GHz	Each	

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